Please add the following new claims:

P

- 18. (New) The method of claim 1, further comprising introducing a photoimageable material layer, wherein the dielectric layer comprising the plurality of different material layers is introduced between the substrate and the photoimageable material layer.
- 19. (New) The method of claim 1, further comprising introducing an etch stop layer between the substrate and the dielectric layer comprising the plurality of different material layers.

500 cs

- 20. (New) The method of claim 1, wherein the dielectric layer comprising the plurality of different material layers is introduced between an etch stop layer and a photoimageable material layer.
- 21. (New) The method of claim 8, further comprising introducing a photoimageable material layer, wherein the dielectric layer comprising the plurality of alternating material layers is introduced between the substrate and the photoimageable material layer.
- 22. (New) The method of claim 8, further comprising introducing an etch stop layer between the substrate and the dielectric layer comprising the plurality of alternating material layers.
- 23. (New) The method of claim 8, wherein the dielectric layer comprising the plurality of alternating material layers is introduced between an etch stop layer and a photoimageable material layer.--

App/No.: 09/750,734

042390.P10050